

IGBT Die

PCFG75T65MQF

Using novel field stop IGBT technology, **onsemi**'s new series of field stop 4th generation IGBTs offer the optimum performance for solar inverter and UPS applications where low conduction and switching losses are essential.

Features

- Maximum Junction Temperature: $T_j = 175^{\circ}\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.42\text{ V (Typ.) @ } I_C = 75\text{ A}$
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution

Typical Applications

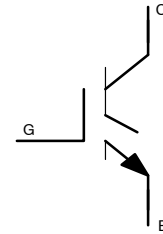
- Solar Inverters
- UPS Systems

MECHANICAL DATA

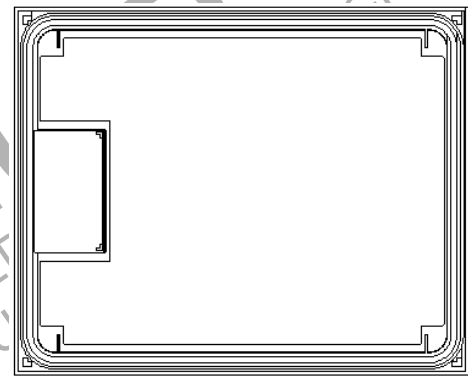
Parameter	Mils	μm
Die Size	208.66 × 169.29	5300 × 4300
Gate Pad Size	31.38 × 56.17	797 × 1426.8
Emitter Pad Size	185.59 × 141.49	4714 × 3593.9
Die Thickness	2.48	63
Scribe Width	80 μm	
Top Metal	5 $\mu\text{m AlSiCu}$	
Back Metal	1.05 $\mu\text{m Al/NiV/Ag}$	
Topside Passivation	Silicon Nitride	
Wafer Diameter	200 mm	
Max Possible Die Per Wafer	1070	
Recommended Storage Environment	In original container, in dry nitrogen, < 3 months at ambient temperature of 23°C	

$V_{RCE} = 650\text{ V}$
 $I_C = \text{Limited by } T_{j(max)}$

IGBT DIE



DIE OUTLINE



ORDERING INFORMATION

Device	Inking?	Shipping Method
PCFG75T65MQF	No	Sawn Wafer on Tape

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MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector to Emitter Voltage, $T_J = 25^\circ\text{C}$	V_{CES}	650	V
Gate to Emitter Voltage	V_{GES}	± 20	V
Collector Current @ $T_C = 25^\circ\text{C}$	I_C	(Note 1)	A
Pulsed Collector Current	I_{CM}	300	A
Operating Junction Temperature	T_J	-40 to +175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-17 to +25	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Depending on the thermal properties of assembly.
2. Not subject to production test – verified by design/characterization.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	BV_{CES}	650			V
Temperature Coefficient of Breakdown Voltage	$I_C = 1\text{ mA}$, reference to 25°C	$\Delta BV_{CES}/\Delta T_J$		0.7		$\text{V}/^\circ\text{C}$
Collector–Emitter Cutoff Current	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	I_{DSS}			250	μA
Gate Leakage Current	$V_{CE} = 0\text{ V}, V_{GE} = V_{GES}$	I_{GSS}			± 400	nA

ON CHARACTERISTICS

G–E Threshold Voltage	$V_{GE} = V_{CE}, I_C = 60\text{ mA}$	$V_{GE(th)}$	2.6	4.6	6.4	V
Collector–Emitter Saturation Voltage	$I_C = 60\text{ A}, V_{GE} = 15\text{ V}$	$V_{CE(sat)}$		1.42	1.9	V
	$I_C = 60\text{ A}, V_{GE} = 15\text{ V}, T_C = 175^\circ\text{C}$			1.7		V

DYNAMIC CHARACTERISTICS

Input Capacitance	$V_{GE} = 0\text{ V}, V_{CE} = 30\text{ V}, f = 1\text{ MHz}$	C_{ies}		4677		pF
Output Capacitance		C_{oes}		63		
Reverse Transfer Capacitance		C_{res}		15		

GATE CHARGE CHARACTERISTICS

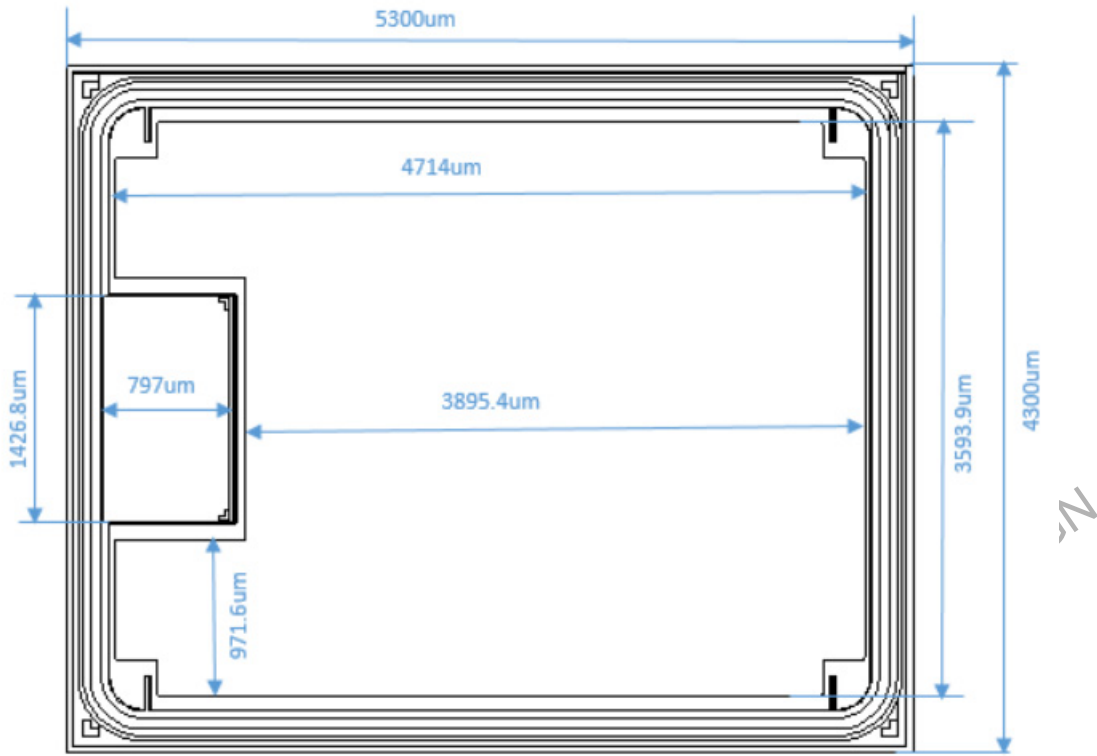
Total Gate Charge	$V_{CE} = 400\text{ V}, I_C = 60\text{ A}, V_{GE} = 15\text{ V}$	Q_g		144		nC
Gate to Emitter Charge		Q_{ge}		26		
Gate to Collector Charge		Q_{gc}		35		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching characteristics and thermal properties are depending strongly on module design and mounting technology.

For ordering, technique and other information on **onsemi** automotive bare die products, please contact automotivebaredie@onsemi.com.

PCFG75T65MQF



(all dimensions in μm)

Figure 1. Die Layout

DISCOM
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